

The following listing of claims will replace all prior versions, and listings, of claims in the application.

**LISTING OF CLAIMS:**

Claim 1 (currently amended): A semiconductor device, comprising:  
a unitary and non-layered semiconductor substrate comprising a thin portion that is thinner than adjacent portions of the semiconductor substrate, and a recessed portion formed below the thin portion;  
wherein the etching rate of the thin portion is slower than that of the surrounding portions of the semiconductor substrate; and  
at least one through hole is formed in the thin portion that extends from the recessed portion, and entirely through the thin portion to the upper surface of the semiconductor substrate ~~thin portion~~.

Claim 2 (cancelled)

Claim 3 (original): The semiconductor device set forth in claim 1, wherein a dopant is infused in the thin portion.

Claim 4 (original): The semiconductor device set forth in claim 1, wherein the thin portion is formed by means of a selective oxide film.

Claims 5-12 (cancelled)